

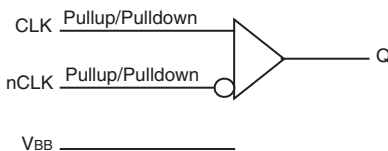
## General Description

830s211 is a 1-to-1 Differential-to- LVCMOS/ LVTTL translator and a member of the family of High Performance Clock Solutions from IDT. The differential input is highly flexible and can accept the following input types: LVPECL, LVDS, LVHSTL, SSTL and HCSL. The small 8-lead SOIC footprint makes this device ideal for use in applications with limited board space.

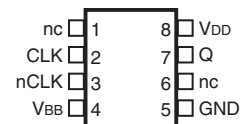
## Features

- One LVCMOS/LVTTL output
- Differential CLK, nCLK input pair
- CLK, nCLK pair can accept the following differential input levels: LVPECL, LVDS, LVHSTL, SSTL, HCSL
- Maximum output frequency: 350MHz
- Part-to-part skew: 525ps (maximum)
- Additive Phase jitter, RMS: 0.11ps (typical)
- Small 8 lead SOIC package saves board space
- Full 3.3V and 2.5V operating supply
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

## Block Diagram



## Pin Assignment



**830s211**

**8-Lead SOIC**

**3.9mm x 4.9mm x 1.375mm package body**

**M Package**

**Top View**

**Table 1. Pin Descriptions**

Number	Name	Type		Description
1, 6	nc	Unused		No connect.
2	CLK	Input	Pullup/ Pulldown	Non-inverting differential clock input.
3	nCLK	Input	Pullup/ Pulldown	Inverting differential clock input.
4	V <sub>BB</sub>	Output		Output reference voltage.
5	GND	Power		Power supply ground.
7	Q	Output		Single-ended clock output. LVCMOS / LVTTTL interface levels.
8	V <sub>DD</sub>	Power		Positive supply pin.

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

**Table 2. Pin Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			4		pF
R <sub>PULLUP</sub>	Input Pullup Resistor			51		kΩ
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ
C <sub>PD</sub>	Power Dissipation Capacitance	V <sub>DD</sub> = 3.465V		10		pF
		V <sub>DD</sub> = 2.625V		8		pF
R <sub>OUT</sub>	Output Impedance	V <sub>DD</sub> = 3.3V		10		Ω
		V <sub>DD</sub> = 2.5V		12		Ω

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, $V_{DD}$	4.6V
Inputs, $V_I$	-0.5V to $V_{DD} + 0.5V$
Outputs, $V_O$	-0.5V to $V_{DD} + 0.5V$
Package Thermal Impedance, $\theta_{JA}$	93.1°C/W (0 mps)
Storage Temperature, $T_{STG}$	-65°C to 150°C

## DC Electrical Characteristics

**Table 3A. Power Supply DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Positive Supply Voltage		3.135	3.3	3.465	V
$I_{DD}$	Power Supply Current				12	mA

**Table 3B. Power Supply DC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Positive Supply Voltage		2.375	2.5	2.625	V
$I_{DD}$	Power Supply Current				11	mA

**Table 3C. LVCMOS/LVTTL DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{OH}$	Output High Voltage; NOTE 1	$V_{DD} = 3.3V$	2.6			V
		$V_{DD} = 2.5V$	1.8			V
$V_{OL}$	Output Low Voltage; NOTE 1	$V_{DD} = 3.3V$ or $2.5V$			0.5	V

NOTE 1: Outputs terminated with  $50\Omega$  to  $V_{DD}/2$ . See Parameter Measurement Information, *Output Load Test Circuit diagrams*.

**Table 3D. Differential DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$I_{IH}$	Input High Current	$V_{DD} = V_{IN} = 3.465V$ or $2.625V$			150	$\mu A$
$I_{IL}$	Input Low Current	$V_{DD} = 3.465V$ or $2.625V$ , $V_{IN} = 0V$	-150			$\mu A$
$V_{PP}$	Peak-to-Peak Voltage; NOTE 1		0.15		1.5	V
$V_{CMR}$	Common Mode Input Voltage; NOTE 1, 2		GND + 0.5		$V_{DD} - 0.85$	V
$V_{BB}$	Output Voltage Reference		$V_{DD} - 1.4$	$V_{DD} - 1.3$	$V_{DD} - 1.2$	V

 NOTE 1:  $V_{IL}$  should not be less than -0.3V.

 NOTE 2: Common mode input voltage is defined as  $V_{IH}$ .

## AC Electrical Characteristics

**Table 4A. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$** 

Parameter	Symbol	Test Conditions	Minimum	Typical	Maximum	Units
$f_{MAX}$	Output Frequency			350		MHz
$t_{PD}$	Propagation Delay, NOTE 1		0.95		1.95	ns
$t_{sk(pp)}$	Part-to-Part Skew; NOTE 2, 3				525	ps
$f_{jit}$	Buffer Additive Phase jitter, RMS; refer to Additive Phase Jitter Section	350MHz, Integration Range (12kHz – 20MHz)		0.11	1	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	85		500	ps
odc	Output Duty Cycle	$f \leq 266MHz$	47		53	%

 NOTE 1: Measured from the differential input crossing point to the output at  $V_{DD}/2$ .

 NOTE 2: Defined as skew between outputs on different devices operating at the same supply voltage and with equal load conditions. Using the same type of input on each device, the output is measured at  $V_{DD}/2$ .

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

**Table 4B. AC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$** 

Parameter	Symbol	Test Conditions	Minimum	Typical	Maximum	Units
$f_{MAX}$	Output Frequency			350		MHz
$t_{PD}$	Propagation Delay, NOTE 1		1		2	ns
$t_{sk(pp)}$	Part-to-Part Skew; NOTE 2, 3				550	ps
$f_{jit}$	Buffer Additive Phase jitter, RMS; refer to Additive Phase Jitter Section	350MHz, Integration Range (12kHz – 20MHz)		0.11	1	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	125		500	ps
odc	Output Duty Cycle	$f \leq 266MHz$	47		53	%

 NOTE 1: Measured from the differential input crossing point to the output at  $V_{DD}/2$ .

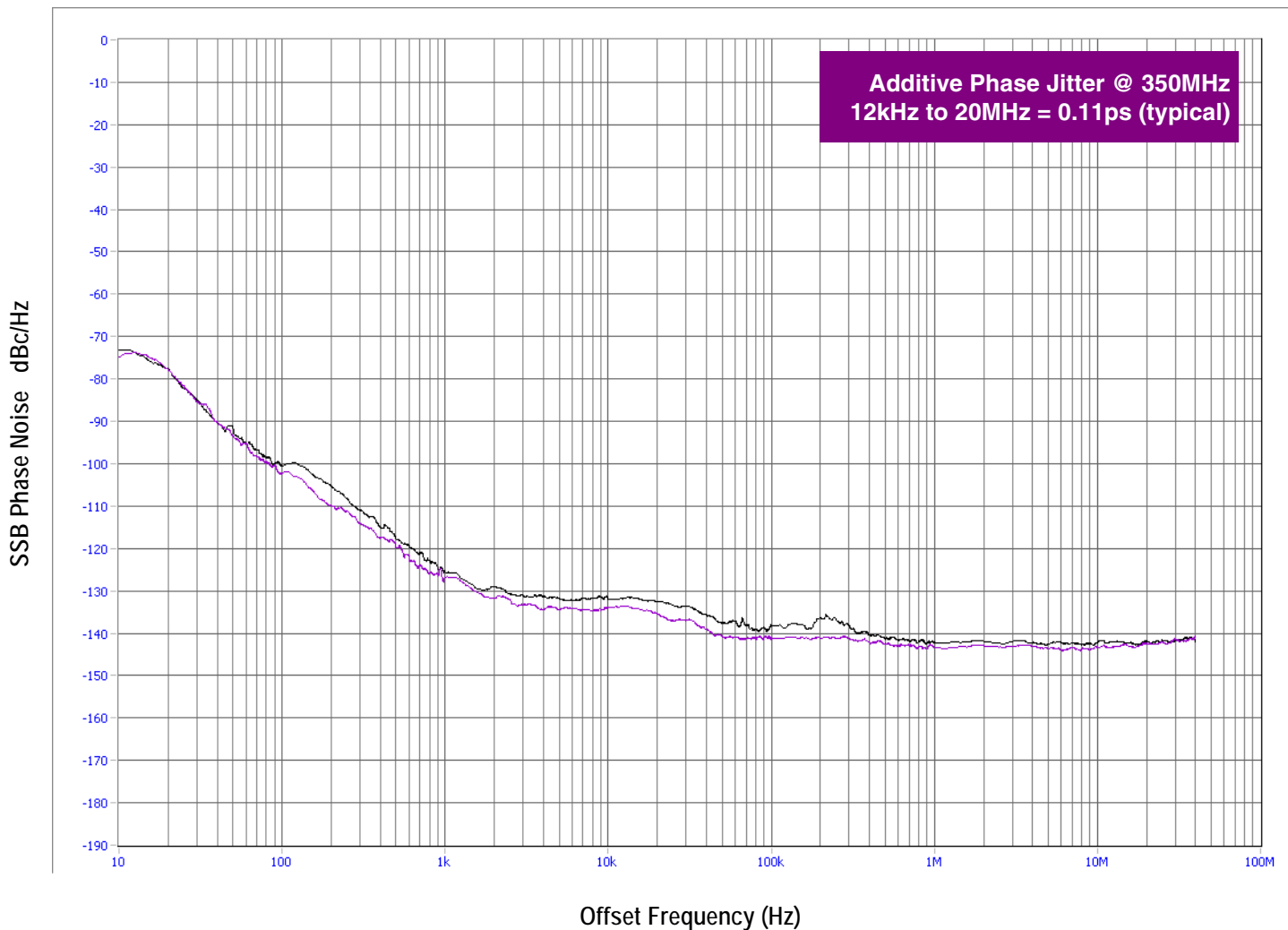
 NOTE 2: Defined as skew between outputs on different devices operating at the same supply voltage and with equal load conditions. Using the same type of input on each device, the output is measured at  $V_{DD}/2$ .

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

## Additive Phase Jitter

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the ***dBc Phase Noise***. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio of the power in the 1Hz band

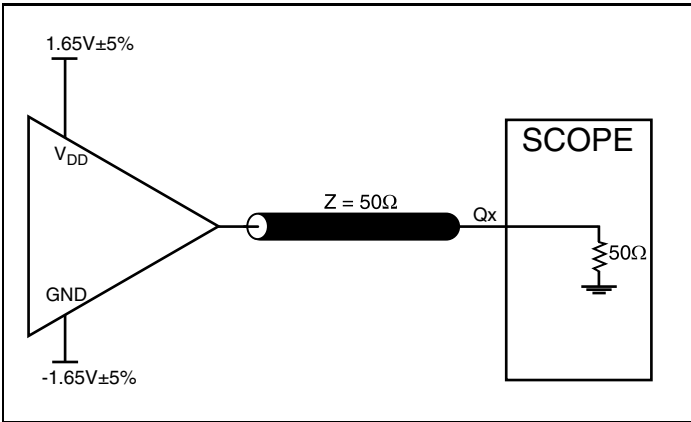
to the power in the fundamental. When the required offset is specified, the phase noise is called a ***dBc*** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



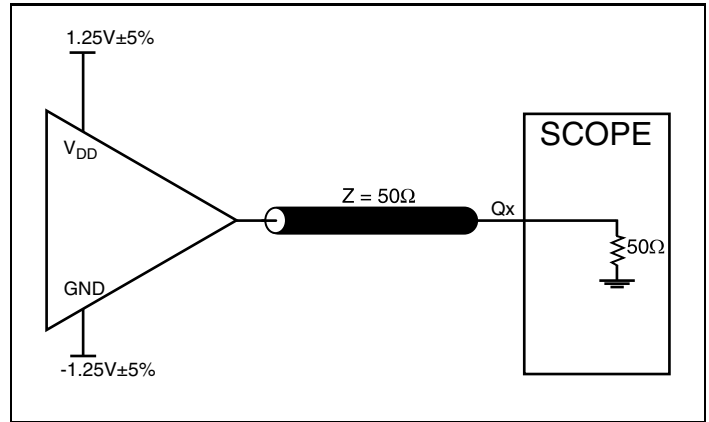
As with most timing specifications, phase noise measurements has issues relating to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device.

This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

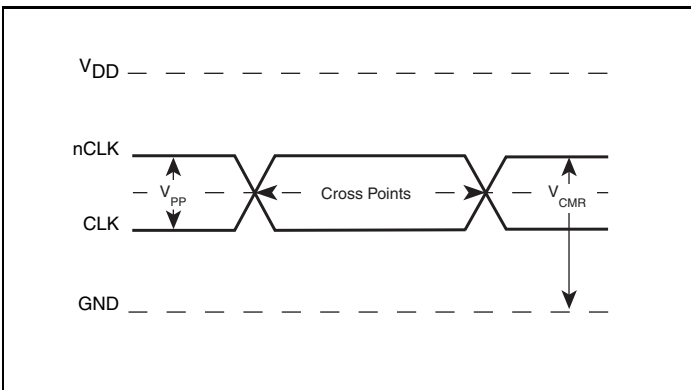
### Parameter Measurement Information



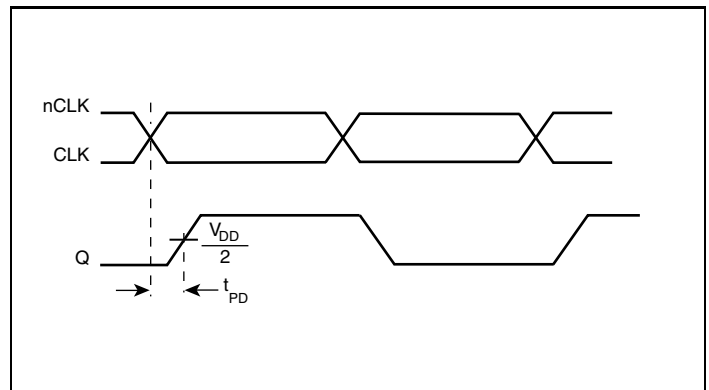
3.3V Core/3.3V LVCMOS Output Load AC Test Circuit



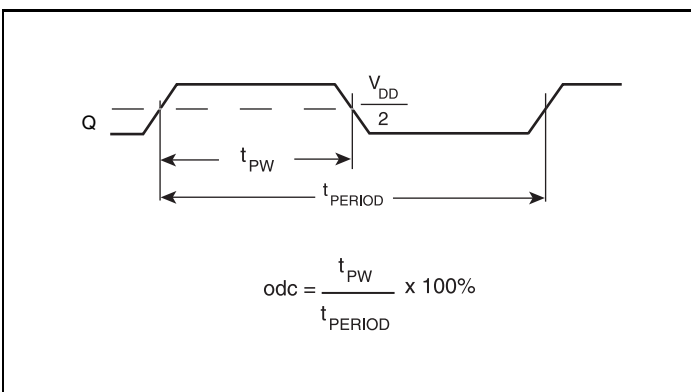
2.5V Core/2.5V LVCMOS Output Load AC Test Circuit



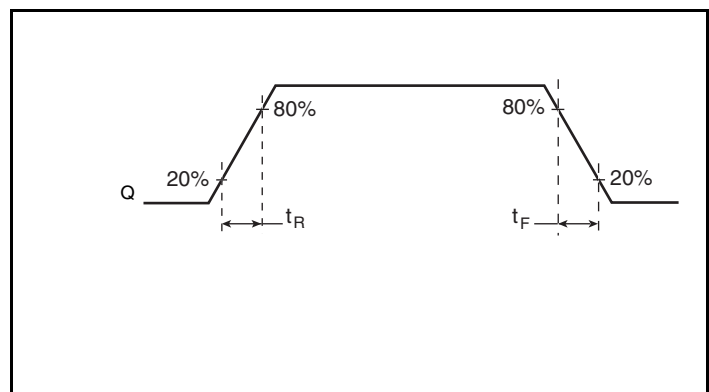
Differential Input Level



Propagation Delay

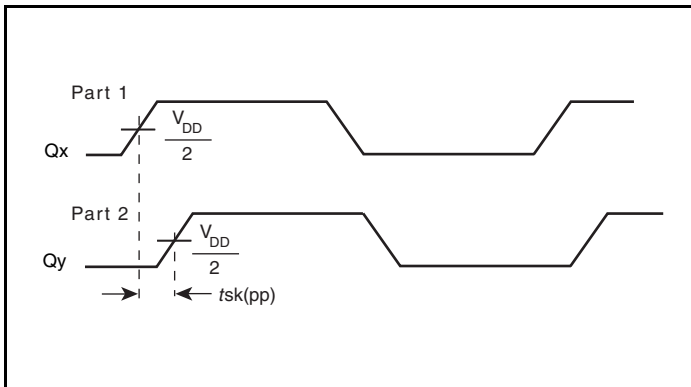


Output Duty Cycle/Pulse Width/Period



Output Rise/Fall Time

## Parameter Measurement Information, continued

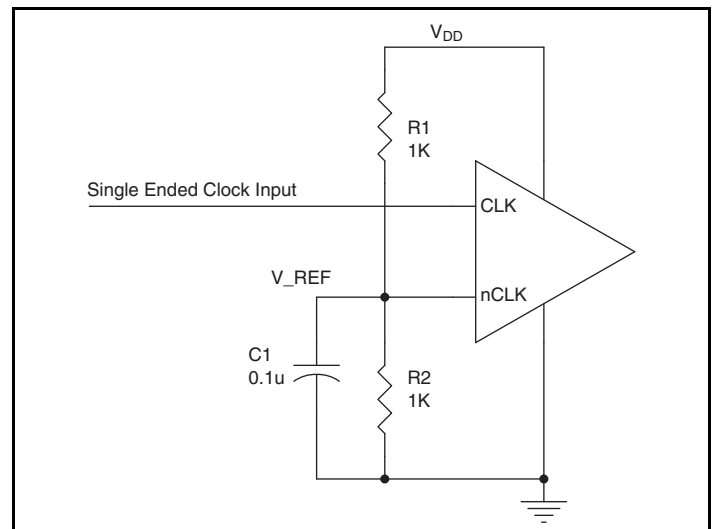


**Part-to-Part Skew**

## Application Information

### Wiring the Differential Input to Accept Single Ended Levels

Figure 1 shows how the differential input can be wired to accept single ended levels. The reference voltage  $V_{REF} = V_{DD}/2$  is generated by the bias resistors R1, R2 and C1. This bias circuit should be located as close as possible to the input pin. The ratio of R1 and R2 might need to be adjusted to position the  $V_{REF}$  in the center of the input voltage swing. For example, if the input clock swing is only 2.5V and  $V_{DD} = 3.3V$ ,  $V_{REF}$  should be 1.25V and  $R2/R1 = 0.609$ .

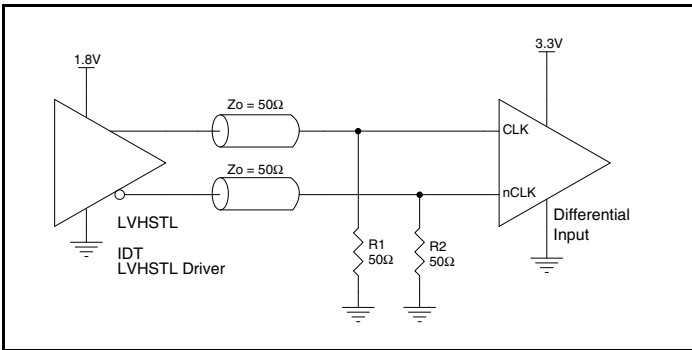


**Figure 1. Single-Ended Signal Driving Differential Input**

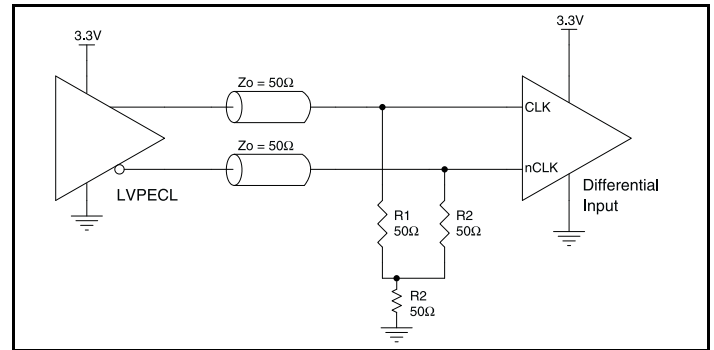
### Differential Clock Input Interface

The CLK /nCLK accepts LVDS, LVPECL, LVHSTL, SSTL, HCSL and other differential signals. Both  $V_{SWING}$  and  $V_{OH}$  must meet the  $V_{PP}$  and  $V_{CMR}$  input requirements. Figures 2A to 2F show interface examples for the HiPerClockS CLK/nCLK input driven by the most common driver types. The input interfaces suggested here are examples only. Please consult with the vendor of the driver

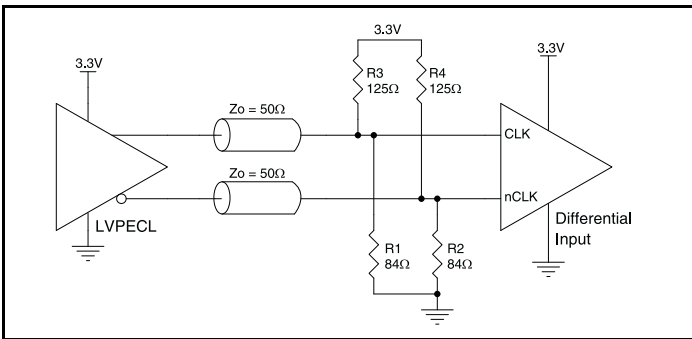
component to confirm the driver termination requirements. For example, in Figure 2A, the input termination applies for IDT HiPerClockS open emitter LVHSTL drivers. If you are using an LVHSTL driver from another vendor, use their termination recommendation.



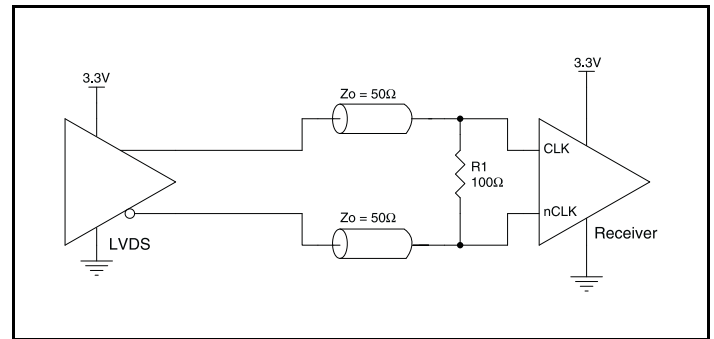
**Figure 2A. HiPerClockS CLK/nCLK Input Driven by an IDT Open Emitter HiPerClockS LVHSTL Driver**



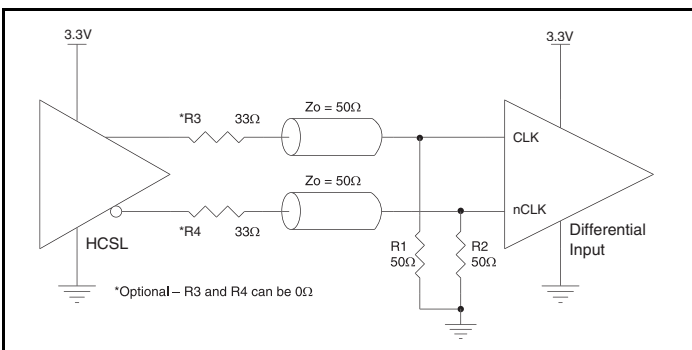
**Figure 2B. HiPerClockS CLK/nCLK Input Driven by a 3.3V LVPECL Driver**



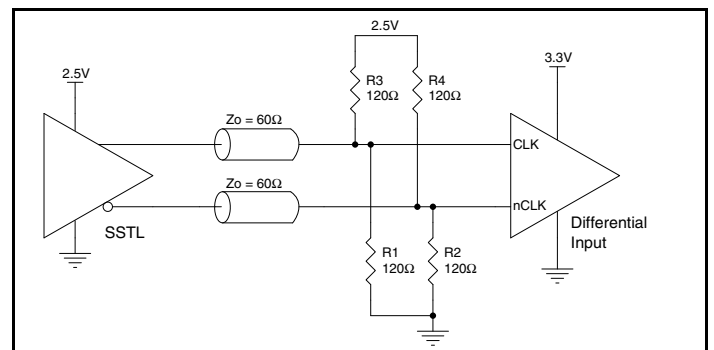
**Figure 2C. HiPerClockS CLK/nCLK Input Driven by a 3.3V LVPECL Driver**



**Figure 2D. HiPerClockS CLK/nCLK Input Driven by a 3.3V LVDS Driver**



**Figure 2E. HiPerClockS CLK/nCLK Input Driven by a 3.3V HCSL Driver**



**Figure 2F. HiPerClockS CLK/nCLK Input Driven by a 2.5V SSTL Driver**



## Reliability Information

Table 5.  $\theta_{JA}$  vs. Air Flow Table for a 8 Lead SOIC

$\theta_{JA}$ vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	93.1°C/W	84.3°C/W	79.6°C/W

## Transistor Count

The transistor count for 830s21I is: 214

## Package Outline and Package Dimensions

Package Outline - M Suffix for 8 Lead SOIC

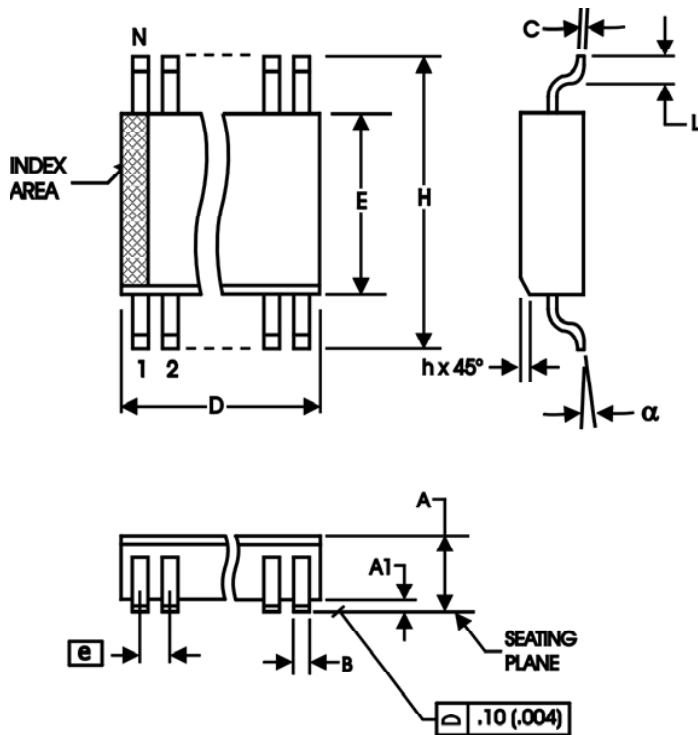


Table 6. Package Dimensions

All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	8	
A	1.35	1.75
A1	0.10	0.25
B	0.33	0.51
C	0.19	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 Basic	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.27
$\alpha$	0°	8°

Reference Document: JEDEC Publication 95, MS-012

## Ordering Information

Table 7. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
830S21AMILF	30S21AIL	"Lead-Free" 8 Lead SOIC	Tube	-40°C to 85°C
830S21AMILFT	30S21AIL	"Lead-Free" 8 Lead SOIC	Tape & Reel	-40°C to 85°C

## Revision History

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Revision Date	Description of Change
December 12, 2015	<ul style="list-style-type: none"> <li>▪ Removed ICS Chip and HiPerClockS under General Description.</li> <li>▪ Removed ICS in the part numbers.</li> <li>▪ Removed LF note at the bottom of the Ordering Information table.</li> <li>▪ Removed the quantity of 2500 from the Tape &amp; Reel in the Ordering information table.</li> <li>▪ Updated datasheet header and footer.</li> </ul>



Corporate Headquarters  
6024 Silver Creek Valley Road  
San Jose, CA 95138 USA  
[www.IDT.com](http://www.IDT.com)

Sales  
1-800-345-7015 or 408-284-8200  
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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

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